



### 20V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 20 V Current 800mA

#### **Features**

- $R_{DS(ON)}$ ,  $V_{GS}$ @4.5V, $I_{DS}$ @500mA=0.4 $\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@2.5V,I<sub>DS</sub>@300mA=0.7Ω
- $R_{DS(ON)}$ ,  $V_{GS}@1.8V$ , $I_{DS}@100mA=1.2\Omega(typ)$
- Advanced Trench Process Technology
- Specially Designed for Load Switch or PWM application.
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

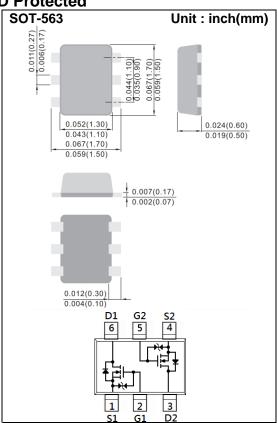
### **Mechanical Data**

• Case: SOT-563 Package

Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.00009 ounces, 0.0026 grams

Marking: X06



# Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12	V
Continuous Drain Current		I <sub>D</sub>	800	mA
Pulsed Drain Current		I <sub>DM</sub>	3000	mA
Power Dissipation	T <sub>A</sub> =25°C	PD	350	mW
	Derate above 25°C		2.8	mW/°C
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55~150	°C
Typical Thermal resistance - Junction to Ambient (Note 3)		$R_{ heta JA}$	357	°C/W





# **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	$BV_{DSS}$	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.4	0.63	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =500mA	-	0.35	0.4	Ω
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =300mA	-	0.6	0.7	
		V <sub>GS</sub> =1.8V,I <sub>D</sub> =100mA	-	1.2		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V,V <sub>GS</sub> =0V	-	0.02	1	uA
Gate-Source Leakage Current	$I_{GSS}$	V <sub>GS</sub> = <u>+</u> 10V,V <sub>DS</sub> =0V	-	<u>+</u> 2	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.92	-	nC
Gate-Source Charge	$Q_gs$		-	0.31	-	
Gate-Drain Charge	$Q_gd$		-	0.08	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	50		pF
Output Capacitance	Coss		-	10		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	8.5		
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	)/ 40\/ L 500A	-	4	-	ns
Turn-On Rise Time	tr	$V_{DD}$ =10V, $I_{D}$ =500mA, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 1.2)	-	20	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	12	-	
Turn-Off Fall Time	tf	R <sub>G</sub> -012	-	25	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			_	-	500	mA
Diode Forward Current	I <sub>S</sub>					
Diode Forward Voltage	$V_{\mathtt{SD}}$	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V		0.91	1.3	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper





#### **TYPICAL CHARACTERISTIC CURVES**

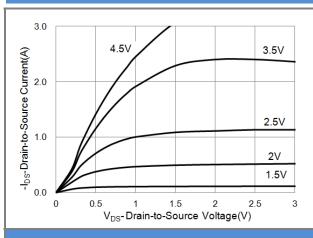
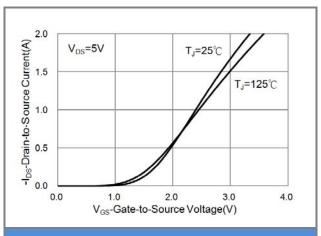


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

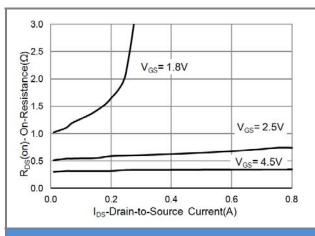


Fig.3 On-Resistance vs. Drain Current

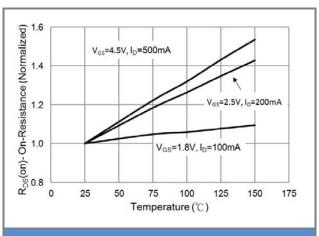


Fig.4 On-Resistance vs. Junction temperature

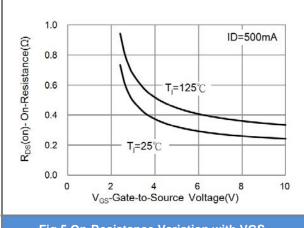


Fig.5 On-Resistance Variation with VGS.

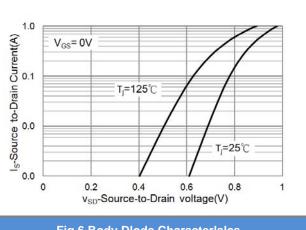


Fig.6 Body Dlode CharacterIslcs





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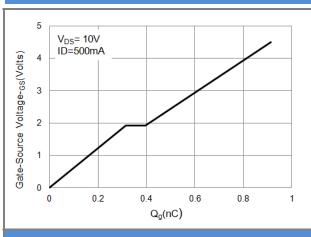


Fig.7 Gate-Charge Characteristics

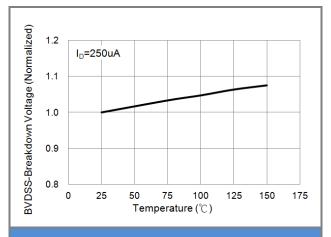


Fig.8 Breakdown Voltage Variation vs. Temperature

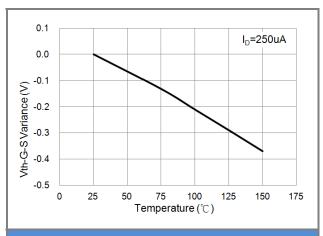


Fig.9 Threshold Voltage Variation with Temperature





### PART NO PACKING CODE VERSION

PART NO PACKING  CODE VERSION	Package Type	Packing type	Marking	Version
PJX8806_R1_00001	SOT-563	4K pcs / 7" reel	X06	Halogen free
PJX8806_R2_00001	SOT-563	10K pcs / 13" reel	X06	Halogen free





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